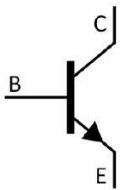


SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

V_{CEO}
High Collector-Emitter Voltage.

High voltage application.

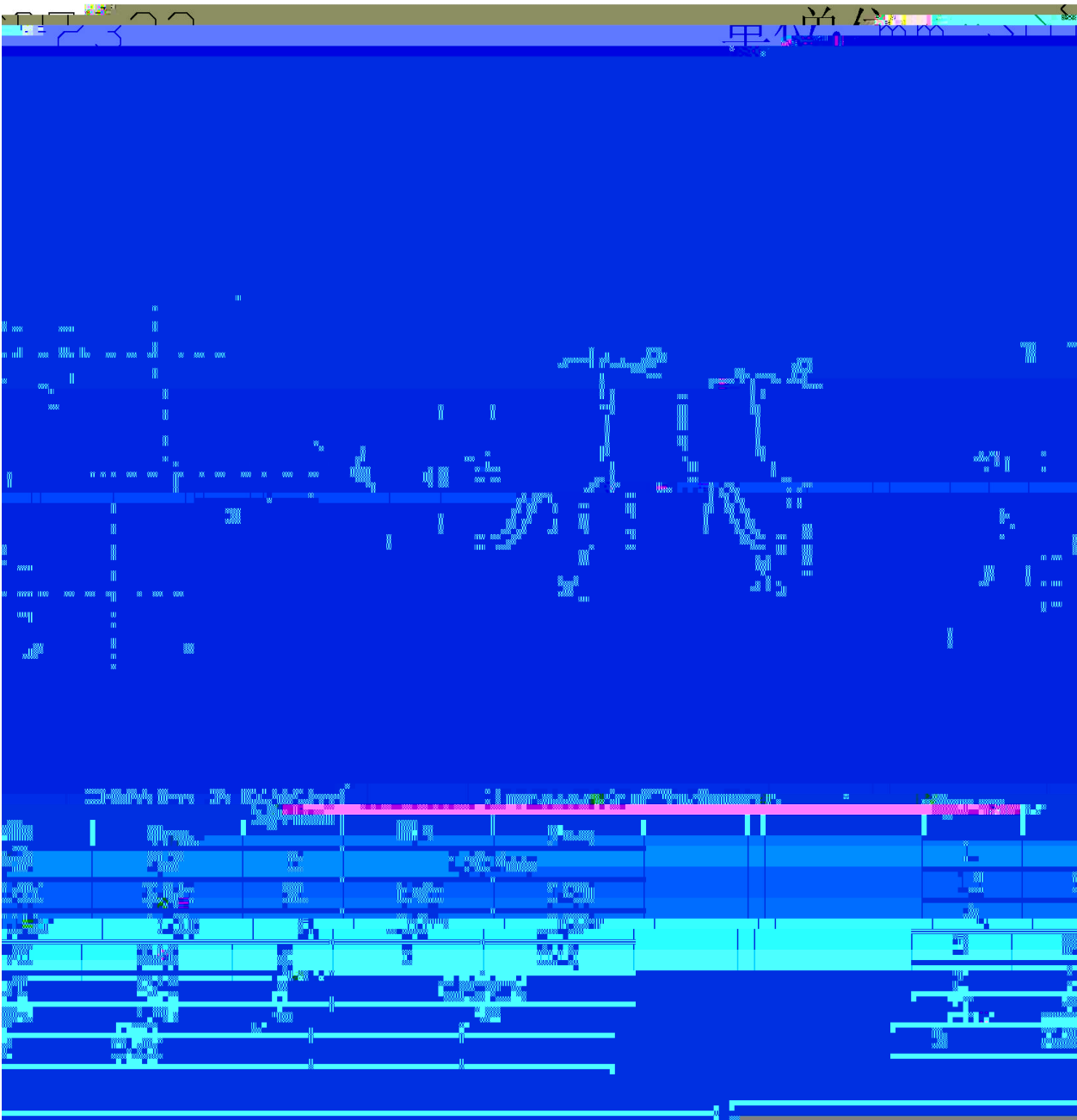


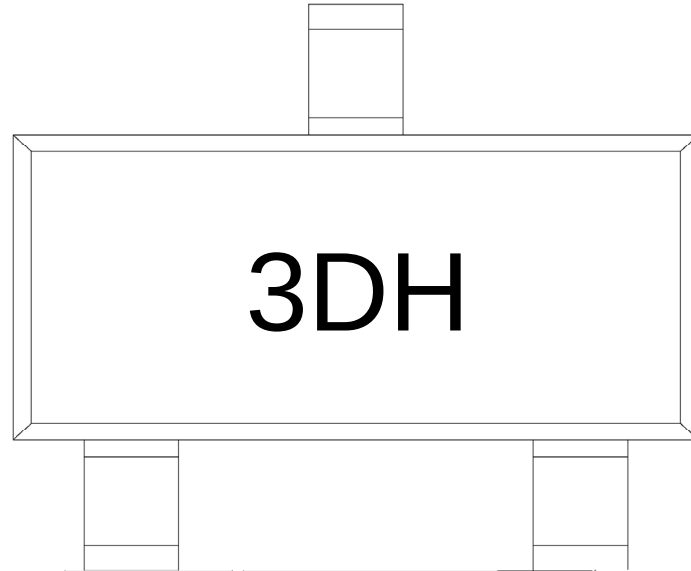
PIN1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Range	30~200
Marking	3DH

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	350	V
Collector to Emitter Voltage	V_{CEO}	350	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55° 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown V						





3D

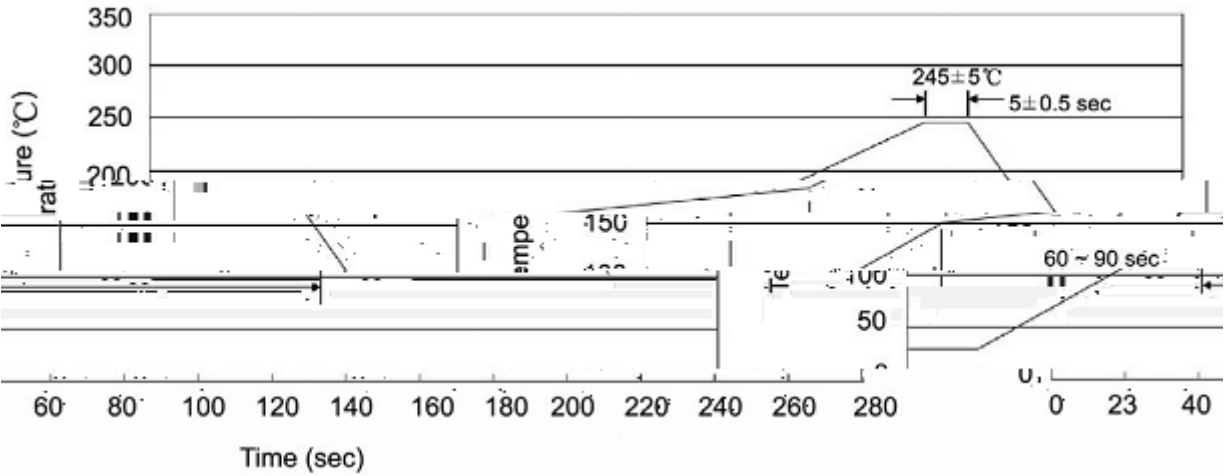
H

Note:

3D Product Type Code

H Company Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ρ ×8	180×120×180	390×385×205